

PBSS5160T

60 V, 1 A PNP low V_{CEsat} (BISS) transistor

Rev. 03 — 18 July 2008

Product data sheet

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NXP Semiconductors

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PBSS5160T

FEATURES

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High efficiency, reduces heat generation
- Reduces printed-circuit board area required
- Cost effective replacement for medium power transistors BCP52 and BCX52.

APPLICATIONS

- Major application segments:
 - Automotive
 - Telecom infrastructure
 - Industrial.
- Power management:
 - DC-to-DC conversion
 - Supply line switching.
- Peripheral driver:
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors).

DESCRIPTION

PNP low V_{CEsat} transistor in a SOT23 plastic package.
NPN complement: PBSS4160T.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PBSS5160T	*U6

Note

1. * = p: made in Hong Kong
* = t: made in Malaysia
* = W: made in China.

ORDERING INFORMATION

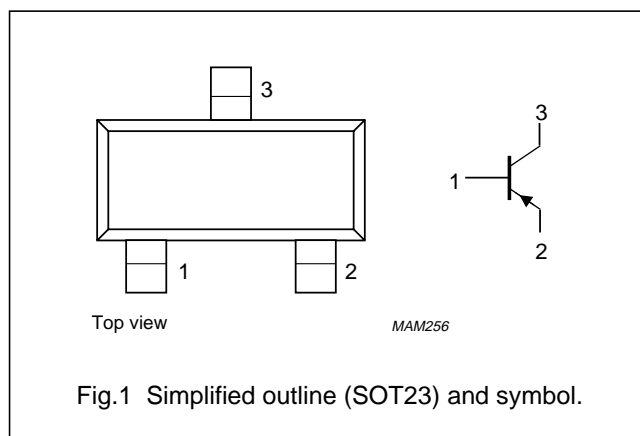
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS5160T	–	plastic surface mounted package; 3 leads	SOT23

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–60	V
I_C	collector current (DC)	–1	A
I_{CM}	peak collector current	–2	A
R_{CEsat}	equivalent on-resistance	330	m Ω

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



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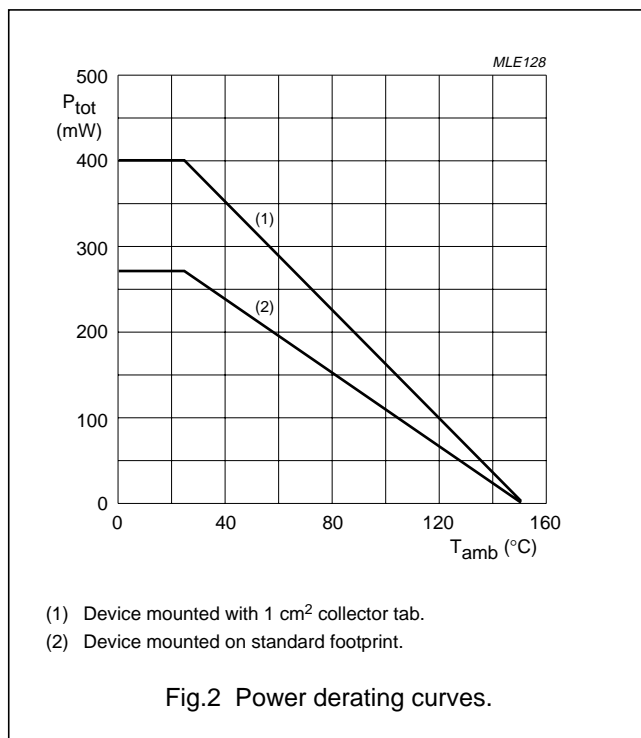
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–80	V
V_{CEO}	collector-emitter voltage	open base	–	–60	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)	note 1	–	–0.9	A
		note 2	–	–1	A
I_{CM}	peak collector current	$t = 1 \text{ ms}$ or limited by $T_{j(max)}$	–	–2	A
I_B	base current (DC)		–	–300	mA
I_{BM}	peak base current	$t_p \leq 300 \mu\text{s}; \delta \leq 0.02$	–	–1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25 \text{ }^\circ\text{C};$ note 1	–	270	mW
		note 2	–	400	mW
		notes 1 and 3	–	1.25	W
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.
2. Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and 1 cm² collector mounting pad.
3. Operated under pulsed conditions: duty cycle $\delta \leq 20 \%$, pulse width $t_p \leq 10 \text{ ms}$.



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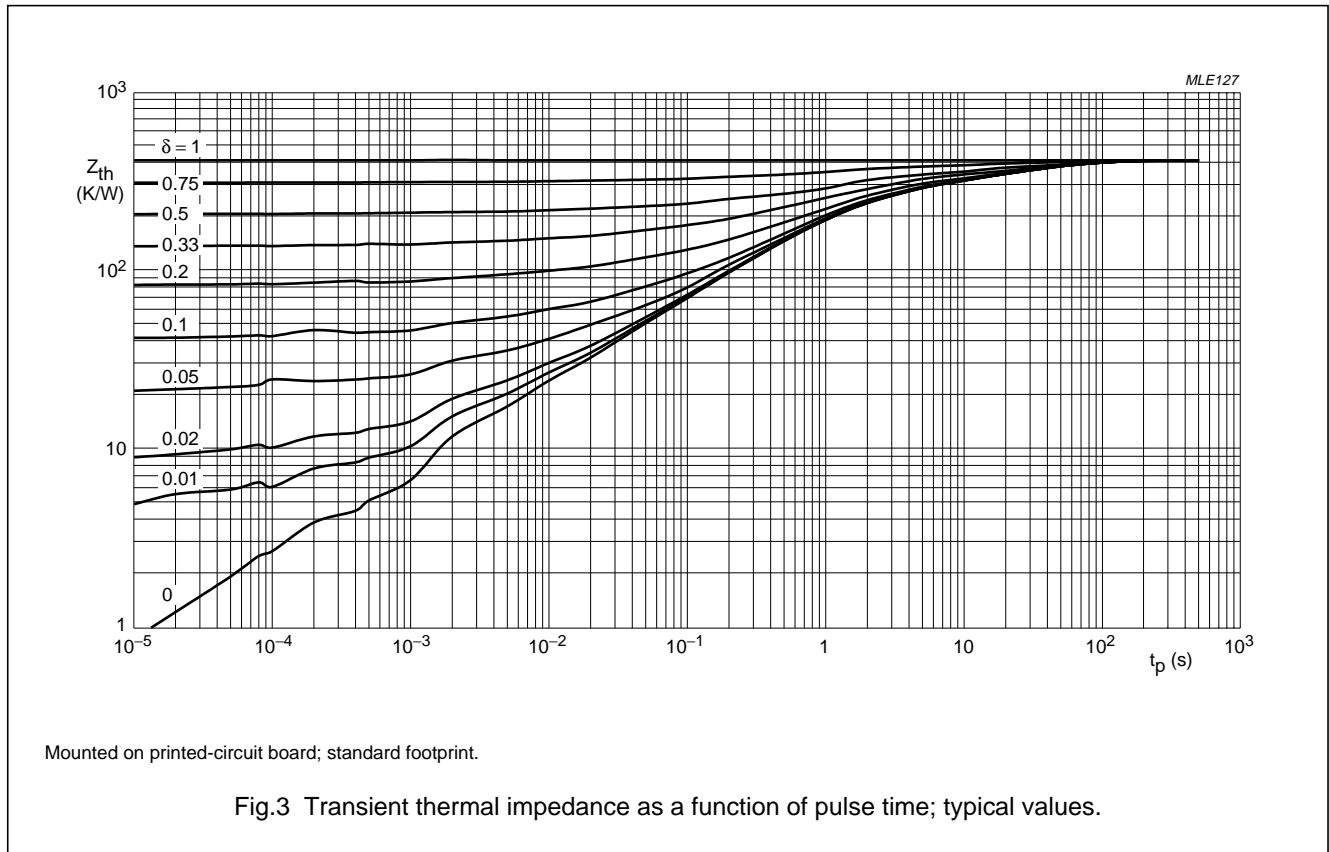
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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; note 1	465	K/W
		in free air; note 2	312	K/W
		in free air; notes 1 and 3	100	K/W

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.
2. Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and 1 cm² collector mounting pad.
3. Operated under pulsed conditions: duty cycle $\delta \leq 20\%$, pulse width $t_p \leq 10$ ms.



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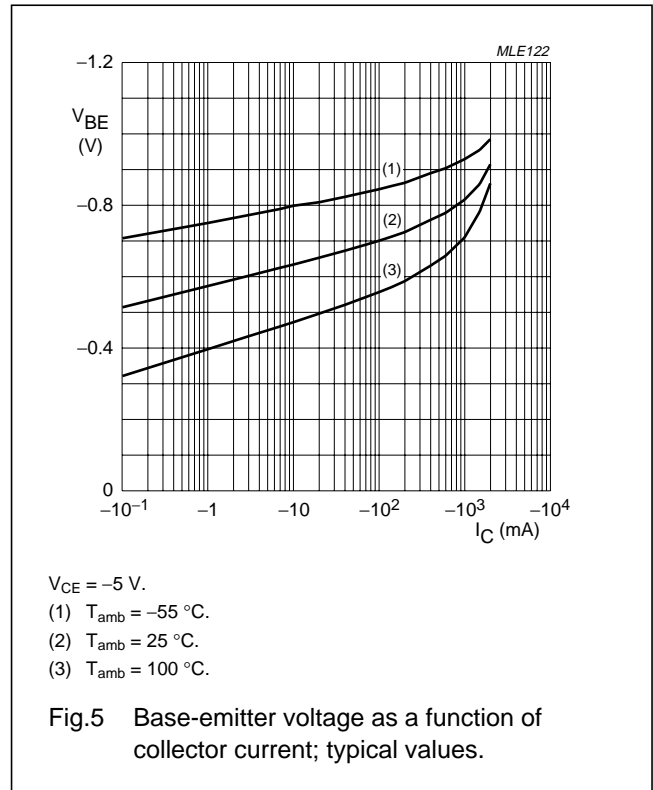
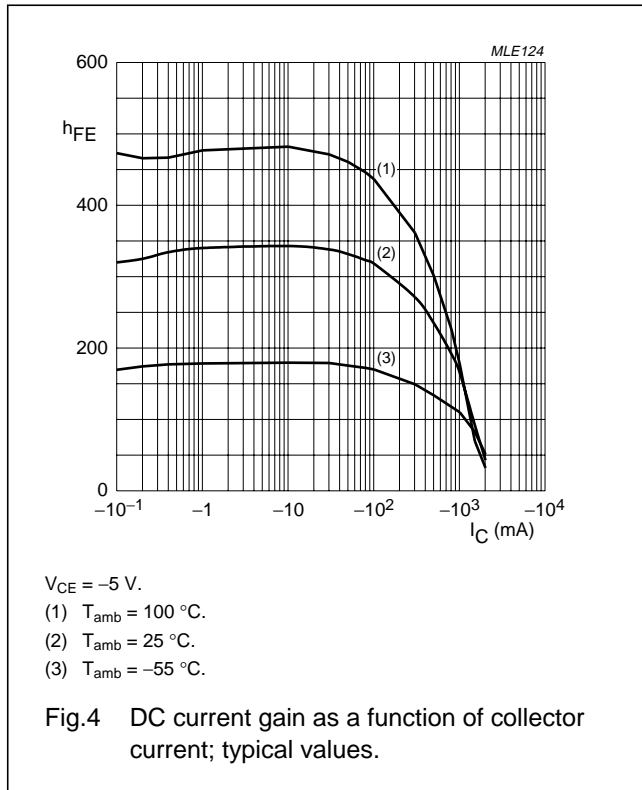
CHARACTERISTICS

$T_{amb} = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -60\text{ V}; I_E = 0\text{ A}$	-	-	-100	nA
		$V_{CB} = -60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^\circ\text{C}$	-	-	-50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = -60\text{ V}; V_{BE} = 0\text{ V}$	-	-	-100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	200	350	-	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}; \text{note 1}$	150	250	-	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}; \text{note 1}$	100	160	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	-	-110	-160	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	-	-120	-175	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}; \text{note 1}$	-	-220	-330	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	-	-0.95	-1.1	V
R_{CEsat}	equivalent on-resistance	$I_C = -1\text{ A}; I_B = -100\text{ mA}; \text{note 1}$	-	220	330	$\text{m}\Omega$
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	-	-0.82	-0.9	V
f_T	transition frequency	$I_C = -50\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	150	220	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	9	15	pF

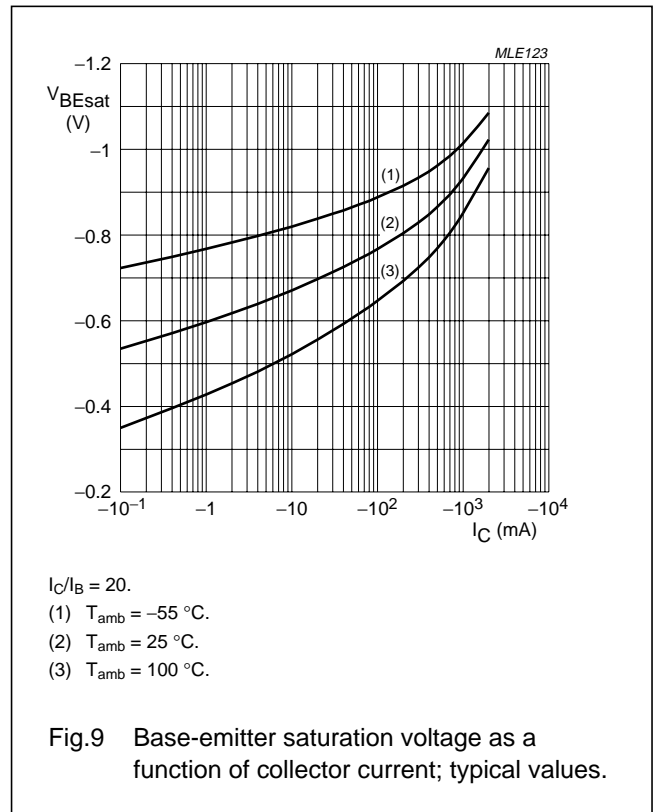
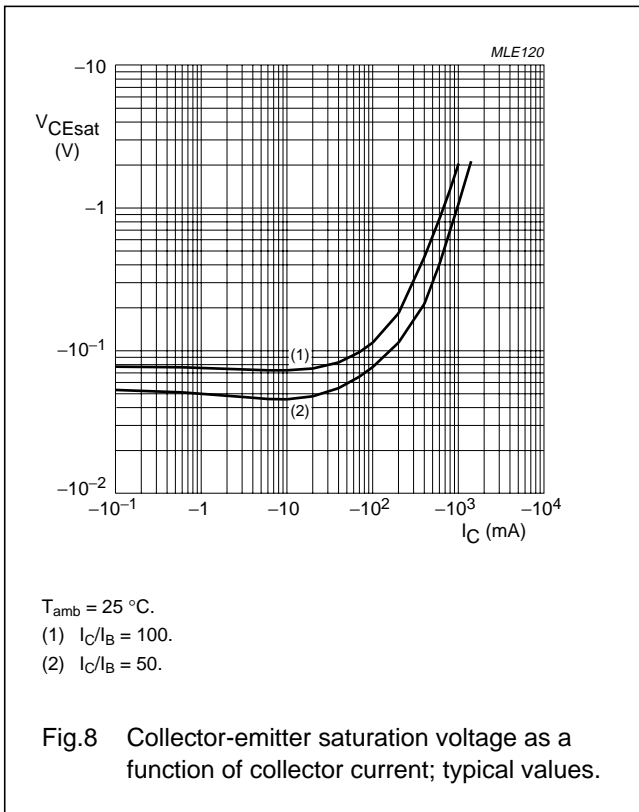
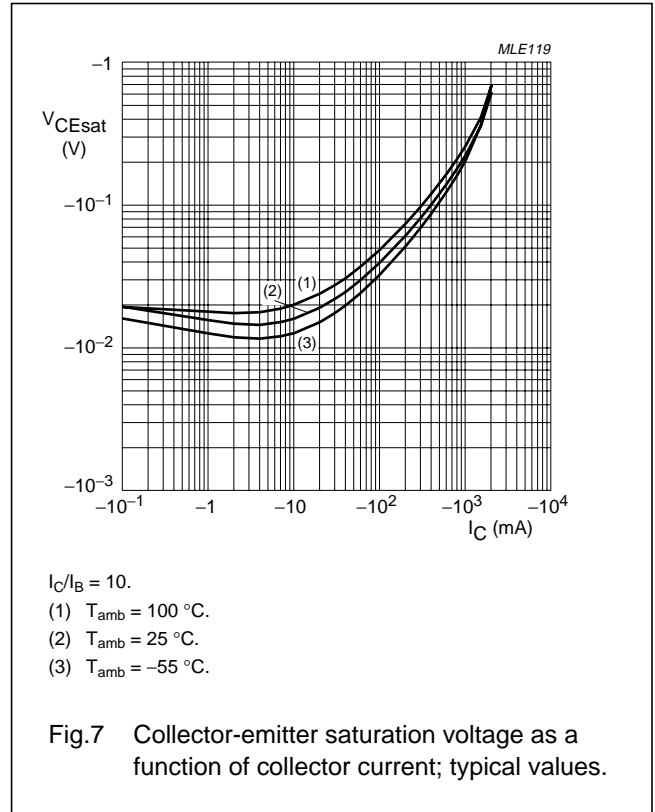
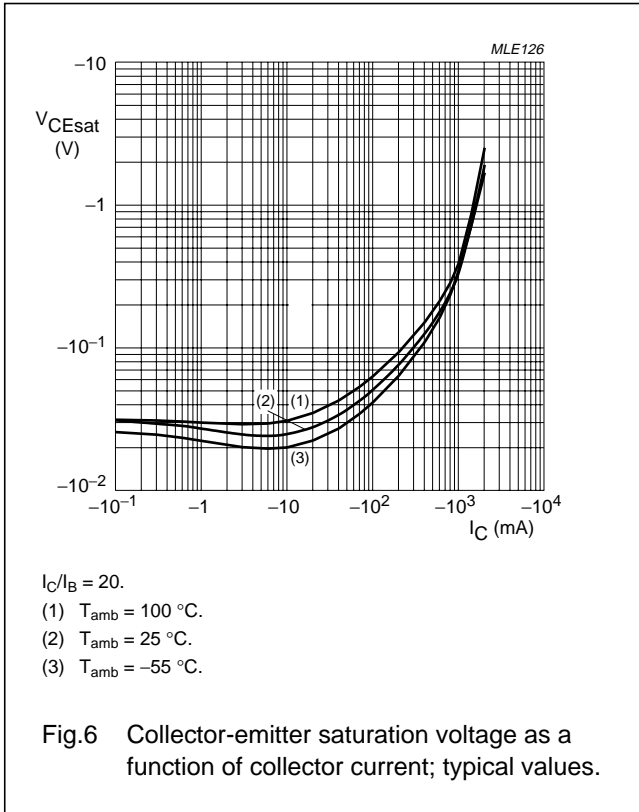
Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.



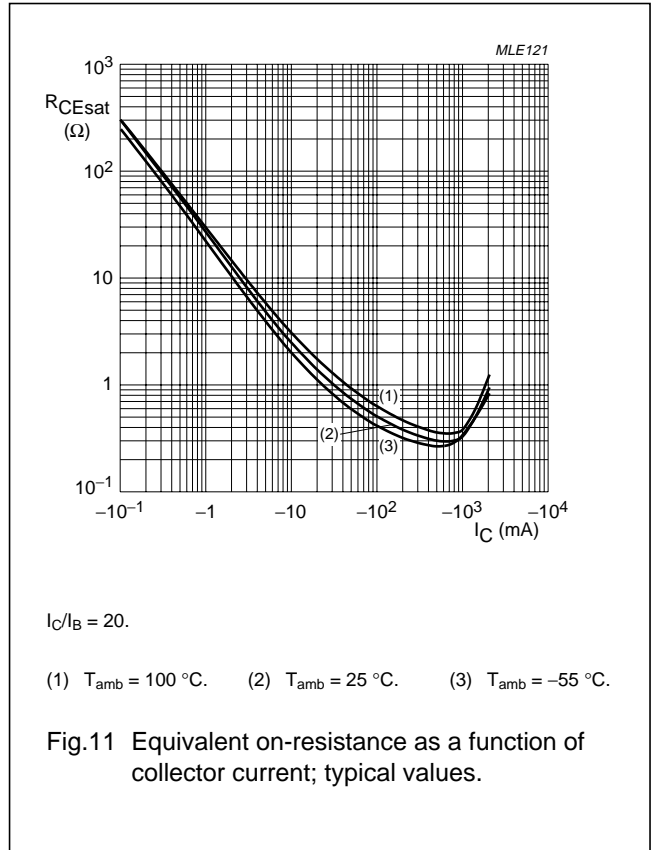
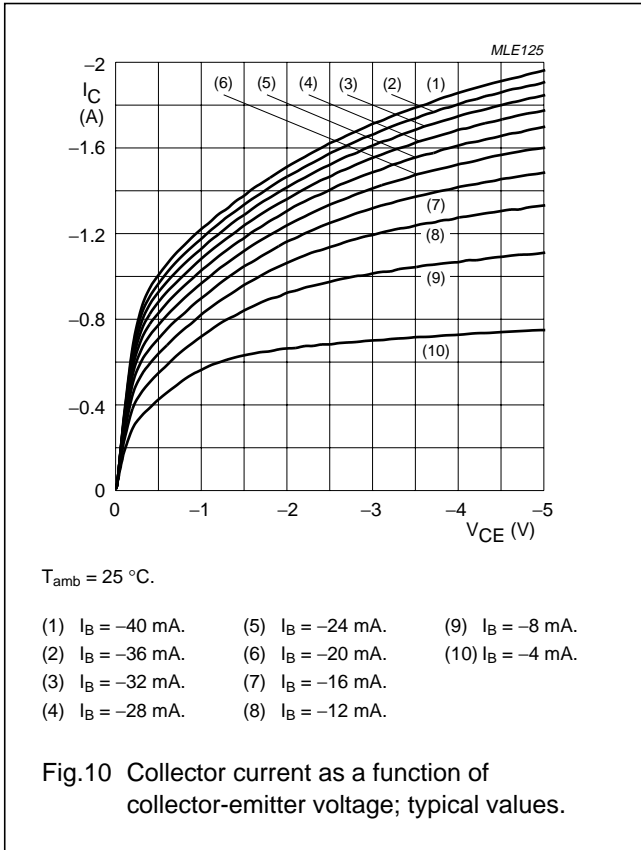
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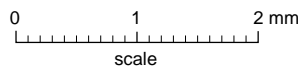
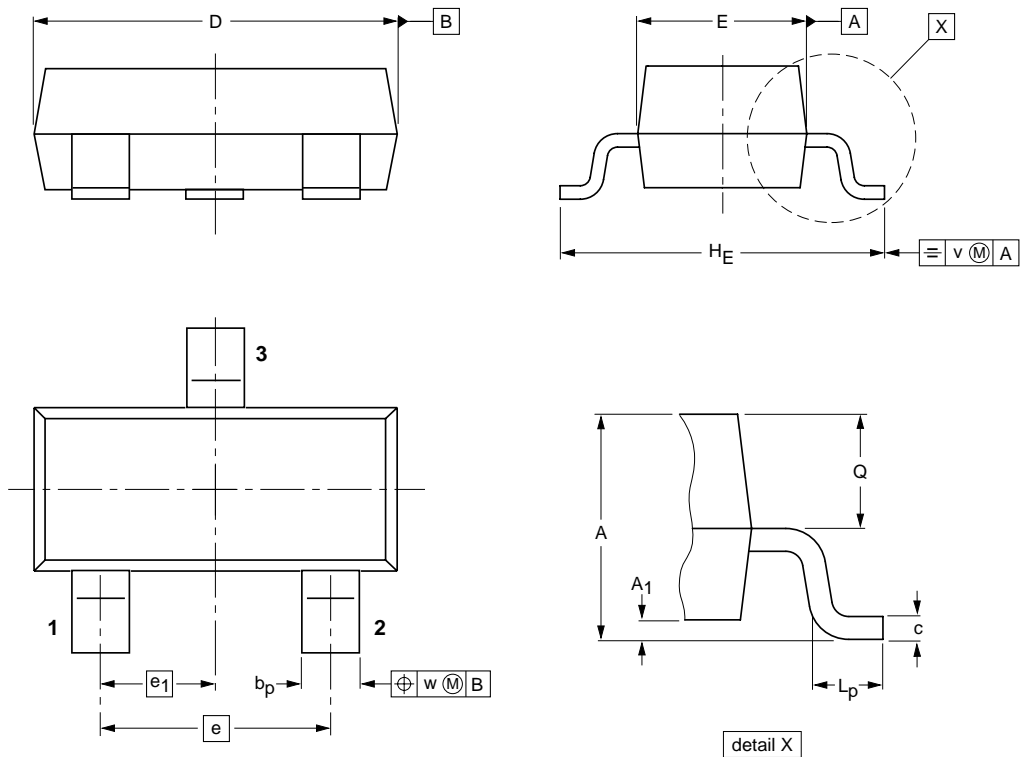
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5160T_N_3	20080718	Product data sheet	-	PBSS5160T_2
Modifications:	• Marking table on page 2; changed code			
PBSS5160T_2 (9397 750 13284)	20040527	Product specification	-	PBSS5160T_1
PBSS5160T_1 (9397 750 11172)	20030623	Product specification	-	-

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